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# July 2008 IGBT®

## FGH40N120AN 1200V NPT IGBT

## **Features**

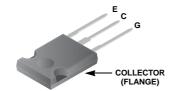
- · High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.6 \text{ V} @ I_C = 40 \text{A}$
- · High input impedance
- · RoHS complaint

## **Applications**

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

## **Description**

Employing NPT technology, Fairchild's AN series of IGBTs provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).





## **Absolute Maximum Ratings**

| Symbol             | Parameter  |                         | FGH40N120AN | Units |  |
|--------------------|--|-------------------------|-------------|-------|--|
| V <sub>CES</sub>   | Collector-Emitter Voltage  |                         | 1200        | V     |  |
| V <sub>GES</sub>   | Gate-Emitter Voltage   |                         | ±25         | V     |  |
|                    | Collector Current  | @T <sub>C</sub> = 25°C  | 64          | A     |  |
| IC                 | Collector Current  | @T <sub>C</sub> = 100°C | 40          | A     |  |
| I <sub>CM(1)</sub> | Pulsed Collector Current   |                         | 160         | A     |  |
| <u> </u>           | Maximum Power Dissipation  | @T <sub>C</sub> = 25°C  | 417         | W     |  |
| $P_{D}$            | Maximum Power Dissipation  | @T <sub>C</sub> = 100°C | 167         | W     |  |
| SCWT               | Short Circuit Withstand Time,<br>V <sub>CE</sub> = 600V, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C |                         | 10          | μs    |  |
| T <sub>J</sub>     | Operating Junction Temperature   |                         | -55 to +150 | °C    |  |
| T <sub>STG</sub>   | Storage Temperature Range  |                         | -55 to +150 | °C    |  |
| T <sub>L</sub>     | Maximum Lead Temp. for Soldering<br>Purposes, 1/8" from Case for 5 seconds                             |                         | 300         | °C    |  |

#### Notes:

(1) Pulse width limited by max. junction temperature

## **Thermal Characteristics**

| Symbol                | Parameter                               | Тур. | Max. | Units |
|-----------------------|---|------|------|-------|
| $R_{\theta JC}(IGBT)$ | Thermal Resistance, Junction-to-Case    |      | 0.3  | °C/W  |
| $R_{\theta JA}$       | Thermal Resistance, Junction-to-Ambient |      | 40   | °C/W  |

## **Package Marking and Ordering Information**

| <b>Device Marking</b> | Device      | Package | Reel Size | Tape Width | Quantity |
|-----------------------|-------------|---------|-----------|------------|----------|
| FGH40N120AN           | FGH40N120AN | TO-247  | =         | =          | 30       |

## Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

| Symbol                                 | Parameter                                    | Conditions   | Min. | Тур. | Max. | Units |
|--|--|--|------|------|------|-------|
| Off Charact                            | eristics                                     |  |      |      |      |       |
| BV <sub>CES</sub>                      | Collector-Emitter Breakdown Voltage          | $V_{GE} = 0V$ , $I_C = 1mA$  | 1200 |      |      | V     |
| BV <sub>CES</sub> /<br>ΔT <sub>J</sub> | Temperature Coefficient of Breakdown Voltage | V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA   |      | 0.6  |      | V/°C  |
| I <sub>CES</sub>                       | Collector Cut-Off Current                    | $V_{CE} = V_{CES}, V_{GE} = 0V$  |      |      | 1    | mA    |
| I <sub>GES</sub>                       | G-E Leakage Current                          | $V_{GE} = V_{GES}, V_{CE} = 0V$  |      |      | ±250 | nA    |
| On Charact                             | eristics                                     |  |      |      |      |       |
| V <sub>GE(th)</sub>                    | G-E Threshold Voltage                        | $I_{C} = 250 \mu A, V_{CE} = V_{GE}$   | 3.5  | 5.5  | 7.5  | V     |
| - GE(III)                              |  | I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V  |      | 2.6  | 3.2  | V     |
| V 0 = ( )                              | Collector to Emitter<br>Saturation Voltage   | I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V,<br>T <sub>C</sub> = 125°C                                       |      | 2.9  |      | V     |
|  |  | I <sub>C</sub> = 64A, V <sub>GE</sub> = 15V  |      | 3.15 |      | V     |
| Dynamic Cl                             | haracteristics                               |  |      | l    |      | 1     |
| C <sub>ies</sub>                       | Input Capacitance                            |  |      | 3200 |      | pF    |
| C <sub>oes</sub>                       | Output Capacitance                           | $V_{CE} = 30V, V_{GE} = 0V$  |      | 370  |      | pF    |
| C <sub>res</sub>                       | Reverse Transfer Capacitance                 | f = 1MHz   |      | 125  |      | pF    |
| Switching (                            | Characteristics                              |  |      |      |      |       |
| t <sub>d(on)</sub>                     | Turn-On Delay Time                           |  |      | 15   |      | ns    |
| t <sub>r</sub>                         | Rise Time                                    |  |      | 20   |      | ns    |
| t <sub>d(off)</sub>                    | Turn-Off Delay Time                          | $V_{CC} = 600V, I_{C} = 40A,$  |      | 110  |      | ns    |
| t <sub>f</sub>                         | Fall Time                                    | $R_G = 5\Omega$ , $V_{GE} = 15V$ ,   |      | 40   | 80   | ns    |
| E <sub>on</sub>                        | Turn-On Switching Loss                       | Inductive Load, T <sub>C</sub> = 25°C  |      | 2.3  | 3.45 | mJ    |
| E <sub>off</sub>                       | Turn-Off Switching Loss                      |  |      | 1.1  | 1.65 | mJ    |
| E <sub>ts</sub>                        | Total Switching Loss                         |  |      | 3.4  | 5.1  | mJ    |
| t <sub>d(on)</sub>                     | Turn-On Delay Time                           |  |      | 20   |      | ns    |
| t <sub>r</sub>                         | Rise Time                                    |  |      | 25   |      | ns    |
| t <sub>d(off)</sub>                    | Turn-Off Delay Time                          | $V_{CC}$ = 600V, $I_{C}$ = 40A,<br>$R_{G}$ = 5 $\Omega$ , $V_{GE}$ = 15V,<br>Inductive Load, $T_{C}$ = 125°C |      | 120  |      | ns    |
| t <sub>f</sub>                         | Fall Time                                    |  |      | 45   |      | ns    |
| E <sub>on</sub>                        | Turn-On Switching Loss                       |  |      | 2.5  |      | mJ    |
| E <sub>off</sub>                       | Turn-Off Switching Loss                      |  |      | 1.8  |      | mJ    |
| E <sub>ts</sub>                        | Total Switching Loss                         |  |      | 4.3  |      | mJ    |
| Q <sub>g</sub>                         | Total Gate charge                            |  |      | 220  |      | nC    |
| Q <sub>ge</sub>                        | Gate-Emitter Charge                          | $V_{CE} = 600V, I_{C} = 40A,$<br>$V_{GE} = 15V$  |      | 25   |      | nC    |
| Q <sub>gc</sub>                        | Gate-Collector Charge                        | 1 *GE = 10 *   |      | 130  |      | nC    |

## **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 

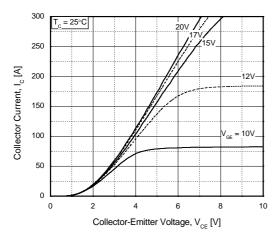


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

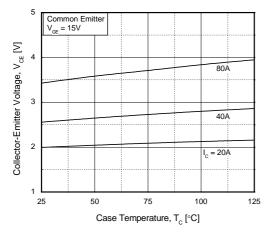


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

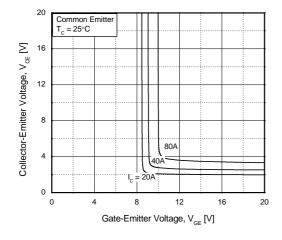


Figure 2. Typical Saturation Voltage Characteristics

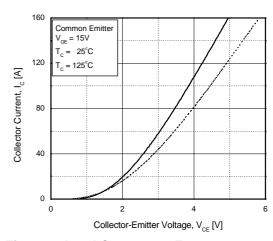


Figure 4. Load Current vs. Frequency

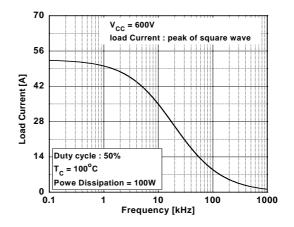
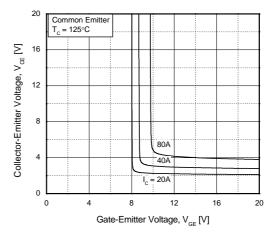


Figure 6. Saturation Voltage vs.  $V_{\text{GE}}$ 



## Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

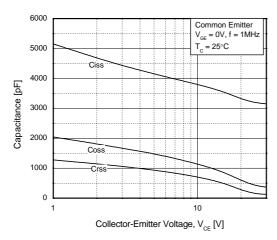


Figure 9. Turn-Off Characteristics vs. Gate Resistance

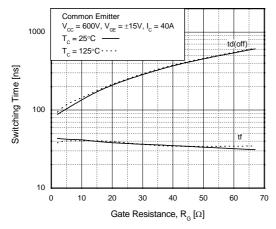


Figure 11. Turn-On Characteristics vs. Collector Current

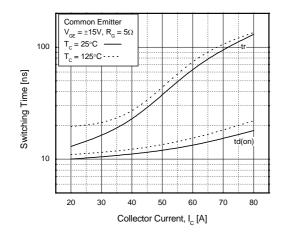


Figure 8. Turn-On Characteristics vs. Gate Resistance

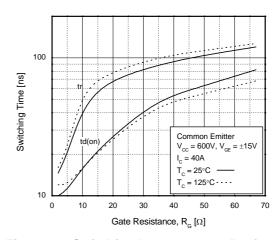


Figure 10. Switching Loss vs. Gate Resistance

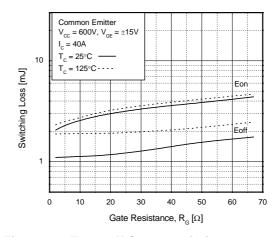
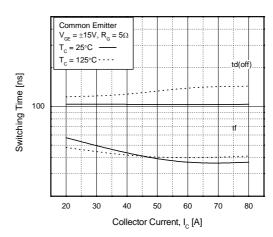


Figure 12. Turn-Off Characteristics vs. Collector Current



## Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

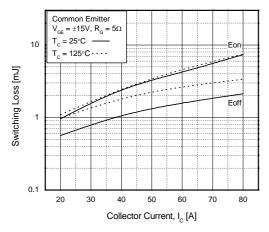


Figure 14. Gate Charge Characteristics

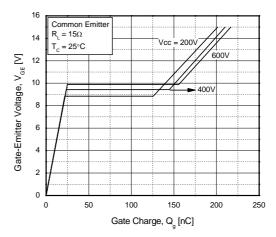


Figure 15. SOA Characteristics

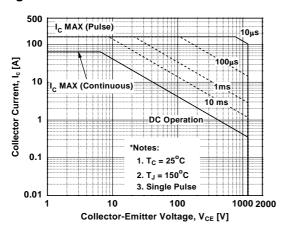


Figure 16. Turn-Off SOA

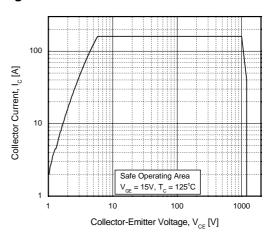
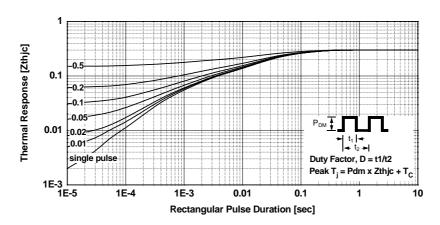
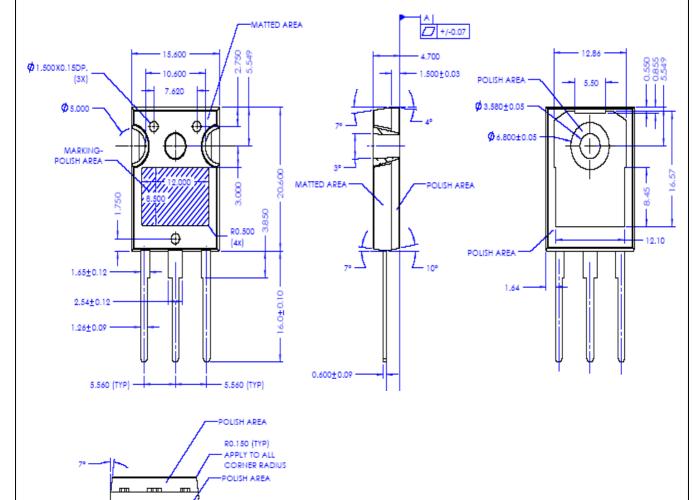


Figure 17. Transient Thermal Impedance of IGBT



## **Mechanical Dimensions**

## TO-247AB (FKS PKG CODE 001)



Dimensions in Millimeters





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